

Kyung Joong Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Highly Efficient and Stable Iridium Oxygen Evolution Reaction Electrocatalysts Based on Porous Nickel Nanotube Template Enabling Tandem Devices with Solar Hydrogen Conversion Efficiency Exceeding 10%. <i>Advanced Science</i> , 2022, 9, e2104938.	11.2	6
2	Uncertainty in the mutual calibration method for the traceable thickness measurement of ultra-thin oxide films. <i>Metrologia</i> , 2021, 58, 034002.	1.2	2
3	Effect of the surface contamination layer on the thickness measurement of ultra-thin HfO ₂ films. <i>Applied Surface Science</i> , 2021, 545, 148982.	6.1	4
4	Calibration of high magnification in the measurement of critical dimension by AFM and SEM. <i>Applied Surface Science</i> , 2021, 565, 150481.	6.1	2
5	Traceable thickness measurement of ultra-thin HfO ₂ films by medium-energy ion scattering spectroscopy. <i>Metrologia</i> , 2020, 57, 025001.	1.2	7
6	Analysis of elemental composition of Fe _{1-x} Ni _x and Si _{1-x} Ge _x alloy thin films by electron probe microanalysis and microfocus X-ray fluorescence. <i>Surface and Interface Analysis</i> , 2020, 52, 929-932.	1.8	2
7	Improvement of power conversion efficiency by a stepwise band-gap structure for silicon quantum dot solar cells. <i>Nanotechnology</i> , 2020, 31, 195404.	2.6	4
8	High efficiency Si quantum dot heterojunction solar cells using a single SiO _x :B layer. <i>Nanotechnology</i> , 2019, 30, 325404.	2.6	5
9	Efficiency improvement of Si quantum dot solar cells by activation with boron implantation. <i>Solar Energy</i> , 2018, 164, 89-93.	6.1	9
10	Quantitative analysis of Si _{1-x} Ge _x alloy films by SIMS and XPS depth profiling using a reference material. <i>Applied Surface Science</i> , 2018, 432, 72-77.	6.1	11
11	Round-robin test for the measurement of layer thickness of multilayer films by secondary ion mass spectrometry depth profiling. <i>Surface and Interface Analysis</i> , 2017, 49, 1057-1063.	1.8	5
12	Band engineering of a Si quantum dot solar cell by modification of B-doping profile. <i>Solar Energy Materials and Solar Cells</i> , 2017, 159, 80-85.	6.2	14
13	Improved electrical properties of silicon quantum dot layers for photovoltaic applications. <i>Solar Energy Materials and Solar Cells</i> , 2016, 150, 71-75.	6.2	10
14	SIMS depth profiling analysis of P-doped n-type Si layer to develop the Si QD solar cell. <i>Surface and Interface Analysis</i> , 2014, 46, 341-343.	1.8	0
15	SIMS study on the improvement of electrical conductivity of a Si quantum dot layer by insertion of polycrystalline Si interlayers. <i>Surface and Interface Analysis</i> , 2014, 46, 337-340.	1.8	0
16	Mechanism of abnormal interface artifacts in SIMS depth profiling of a Si/Ge multilayer by oxygen ions. <i>Surface and Interface Analysis</i> , 2014, 46, 267-271.	1.8	4
17	Determination of interface locations and layer thicknesses in SIMS and AES depth profiling of Si/Ti multilayer films by 50 at% definition. <i>Surface and Interface Analysis</i> , 2014, 46, 272-275.	1.8	3
18	Accurate quantification of Cu(In,Ga)Se ₂ films by AES depth profiling analysis. <i>Applied Surface Science</i> , 2013, 282, 777-781.	6.1	5

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19	Thickness measurement of a thin hetero-oxide film with an interfacial oxide layer by X-ray photoelectron spectroscopy. <i>Applied Surface Science</i> , 2012, 258, 3552-3556.	6.1	15
20	Energy dispersive electron probe microanalysis (ED-EPMA) of elemental composition and thickness of Fe-Ni alloy films. <i>Surface and Interface Analysis</i> , 2012, 44, 1459-1461.	1.8	25
21	A method to determine the interface position and layer thickness in SIMS depth profiling of multilayer films. <i>Metrologia</i> , 2010, 47, 253-261.	1.2	20
22	Determination of the Absolute Thickness of Ultrathin Al ₂ O ₃ Overlayers on Si (100) Substrate. <i>Analytical Chemistry</i> , 2009, 81, 8519-8522.	6.5	23
23	A mutual calibration method to certify the thickness of nanometre oxide films. <i>Metrologia</i> , 2008, 45, 507-511.	1.2	14
24	Ultra-thin SiO ₂ on Si VIII. Accuracy of method, linearity and attenuation lengths for XPS. <i>Surface and Interface Analysis</i> , 2007, 39, 512-518.	1.8	31
25	Quantitative depth profiling of an alternating Pt/Co multilayer and a Pt-Co alloy multilayer by SIMS using a Buckminsterfullerene (C ₆₀) source. <i>Applied Surface Science</i> , 2007, 253, 6000-6005.	6.1	20
26	Thickness measurement of SiO ₂ films thinner than 1 nm by X-ray photoelectron spectroscopy. <i>Thin Solid Films</i> , 2006, 500, 356-359.	1.8	45
27	In-situ Control of Nitrogen Content and the Effect on PL Properties of SiN _x Films Grown by Ion Beam Sputter Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2004, 817, 86.	0.1	0
28	Formation of a highly oriented FeO thin film by phase transition of Fe ₃ O ₄ and Fe nanocrystallines. <i>Thin Solid Films</i> , 2000, 360, 118-121.	1.8	74
29	Surface topography development on ion-beam-sputtered surfaces: Role of surface inhomogeneity induced by ion-beam bombardment. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996, 14, 2744-2756.	2.1	16
30	Significant improvement in depth resolution of Cr/Ni interfaces by secondary ion mass spectrometry profiling under normal O ₂ ⁺ ion bombardment. <i>Applied Physics Letters</i> , 1992, 60, 1178-1180.	3.3	25
31	Traceable quantitative analysis of Ag _x Cu _{1-x} alloy films by ID ICP-MS, RBS and MEIS. <i>Metrologia</i> , 0, , .	1.2	1
32	Review on the thickness measurement of ultrathin oxide films by mutual calibration method. <i>Surface and Interface Analysis</i> , 0, , .	1.8	3